

IN THE CLAIMS

Claims 1-9 (Canceled).

10. (Currently Amended) An integrated circuit comprising:
a semiconductor structure;
a first trench formed of a first depth in said semiconductor structure;
a covering on said first trench and over said semiconductor structure, said covering being thicker in said first trench than over said semiconductor structure; and
said covering having an opening through a portion of said covering that is over said semiconductor structure, said opening and above a portion of said first trench to define a region for a second trench.

11. (Original) The circuit of claim 10 wherein said covering is spin-on glass.

Claims 12-15 (Canceled).

16. (Previously Presented) The circuit of claim 10 wherein said opening is a second trench.

17. (Previously Presented) The circuit of claim 16 wherein said second trench extends transversely to said first trench.

18. (Previously Presented) The circuit of claim 17 wherein said second trench is shallower than said first trench.